

ABSTRACT

A wafer provided with a resist pattern is placed in a dry etching apparatus, and an antireflection film and a silicon nitride film are dry-etched using the resist pattern as a mask. Thus, a first deposit deposited on a side face of the resist pattern facing inwardly with respect 5 to the center of the wafer, and a second deposit deposited on a side face of the resist pattern facing outwardly are both relatively thickly adhered. An etching gas used in this case is a gas mixture containing SF₆, CHF₃ and Ar.